

Amirhossein Bayani

List of Publications by Year in descending order

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18
papers

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1305906

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all docs

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docs citations

18
times ranked

209
citing authors

#	ARTICLE	IF	CITATIONS
1	A Scheme of Quantum Tunnel Field Effect Transistor Based on Armchair Graphene Nano-Ribbon. ECS Journal of Solid State Science and Technology, 2021, 10, 091012.	0.9	2
2	Electronic and optical properties of 14,14,18 graphyne as an anti-visible ray coating. Optik, 2020, 203, 163905.	1.4	4
3	Theoretical investigation on $\text{BeN}_{\{2\}}$ monolayer for an efficient bifunctional water splitting catalyst. Scientific Reports, 2020, 10, 21411.	1.6	6
4	The influence by substrate morphology on the Rashba band splitting in graphene. Results in Physics, 2020, 17, 103065.	2.0	1
5	Intercalation of Au Atoms into SiC(0001)/Buffer Interfacesâ€“A First-Principles Density Functional Theory Study. ACS Omega, 2020, 5, 14842-14846.	1.6	3
6	The morphology of an intercalated Au layer with its effect on the Dirac point of graphene. Scientific Reports, 2020, 10, 1042.	1.6	11
7	Simulation of Field Effect Sensor Based on Graphene Nanoribbon to Detect Toxic NO Gas. Silicon, 2018, 10, 2695-2699.	1.8	4
8	Tuning the analog and digital performance of Germanene nanoribbon field effect transistors with engineering the width and geometry of source, channel and drain region in the ballistic regime. Materials Science in Semiconductor Processing, 2018, 80, 18-23.	1.9	11
9	Effective mass approximation versus full atomistic model to calculate the output characteristics of a gate-all-around germanium nanowire field effect transistor (GAA-GeNW-FET). Superlattices and Microstructures, 2018, 113, 769-776.	1.4	10
10	Benchmarking Performance of a Gate-All-Around Germanium Nanotube Field Effect Transistor (GAA-GeNTFET) against GAA-CNTFET. ECS Journal of Solid State Science and Technology, 2017, 6, M24-M28.	0.9	12
11	Simulation Investigation of Siligene Nanoribbon as a Novel Gas Sensor with Strain Engineering: Sensitivity and Selectivity of Current-Voltage Characteristic. ECS Journal of Solid State Science and Technology, 2017, 6, M83-M87.	0.9	1
12	Investigation of sub-10nm cylindrical surrounding gate germanium nanowire field effect transistor with different cross-section areas. Superlattices and Microstructures, 2017, 105, 110-116.	1.4	19
13	Hydrogen sensitive field-effect transistor based on germanene nanoribbon and optical properties of hydrogenated germanene. Journal of Computational Electronics, 2016, 15, 381-388.	1.3	16
14	The effect of concentration of H ₂ physisorption on the currentâ€“voltage characteristic of armchair BN nanotubes in CNTâ€“BNNTâ€“CNT set. Pramana - Journal of Physics, 2016, 87, 1.	0.9	8
15	Impact of uniaxial compressive strain on physical and electronic parameters of a 10Ånm germanene nanoribbon field effect transistor. Superlattices and Microstructures, 2016, 100, 198-208.	1.4	17
16	CO gas optoelectronic sensor using semiconductor graphene nanoribbons: A firstâ€“principles study. Physica Status Solidi (B): Basic Research, 2016, 253, 559-565.	0.7	3
17	Germanene nanoribbon tunneling field effect transistor (GeNR-TFET) with a 10 nm channel length: analog performance, doping and temperature effects. Semiconductor Science and Technology, 2016, 31, 045009.	1.0	27
18	The study of the effect of increasing adsorbed hydrogen's atomic percentage on electronic properties of boron-nitride nanotube. Physica E: Low-Dimensional Systems and Nanostructures, 2013, 53, 168-172.	1.3	5